

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)TYP}$ | I_D |
|---------------|-----------------|-------|
| 20V | 60mΩ@4.5V | 1.2A |
| | 70mΩ@2.5V | |

Feature

- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

Applications

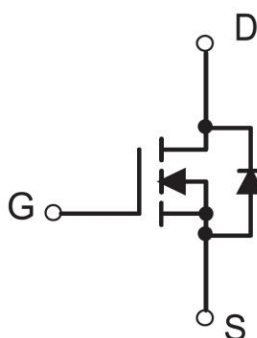
- Load Switch
- Portable Devices
- DCDC conversion

Package

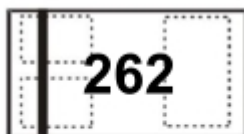


DFN1006-3L

Circuit diagram



Marking



262 =Device Code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|------------------|-----------|------|
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage | V _{GS} | ±12 | V |
| Continuous Drain Current | I _D | 1.2 | A |
| Pulsed Drain Current | I _{DM} | 2.4 | A |
| Power Dissipation | P _D | 0.15 | W |
| Thermal Resistance from Junction to Ambient | R _{θJA} | 833 | °C/W |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{STG} | -55~ +150 | °C |

Electrical characteristics

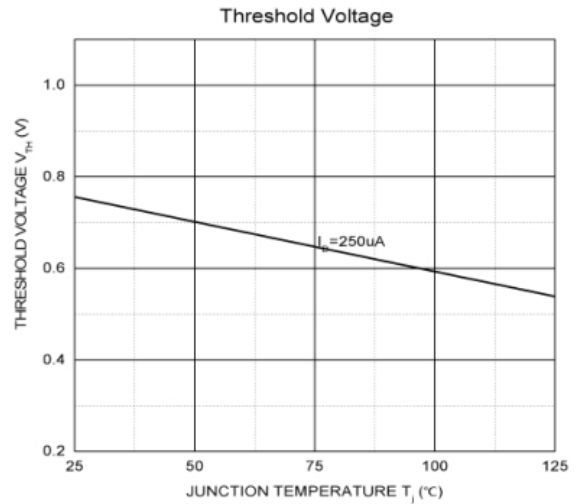
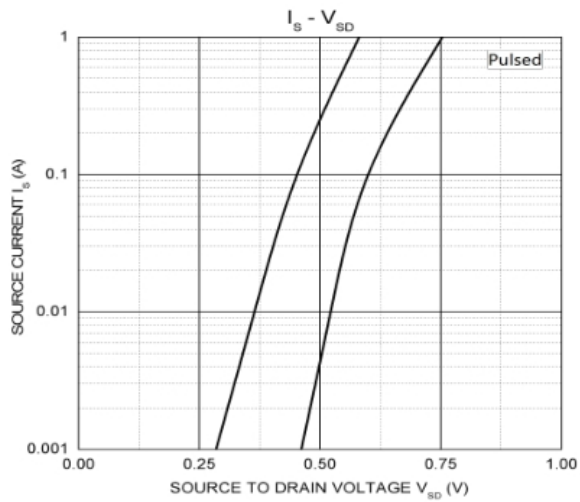
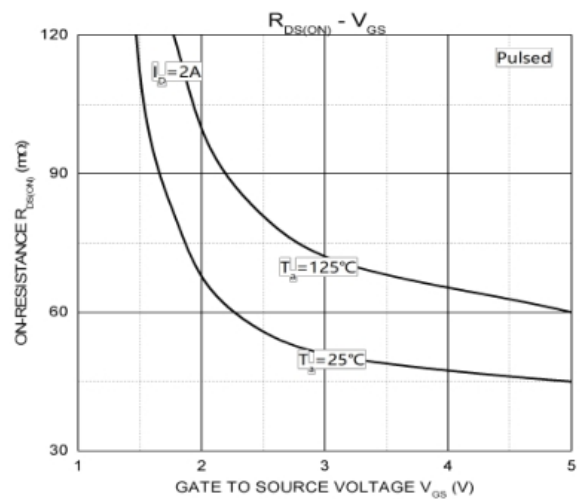
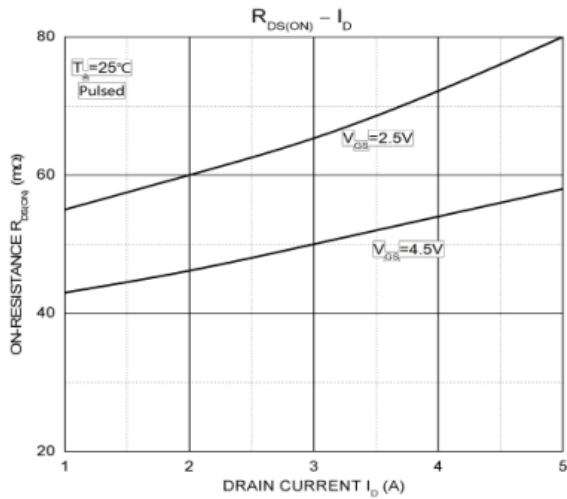
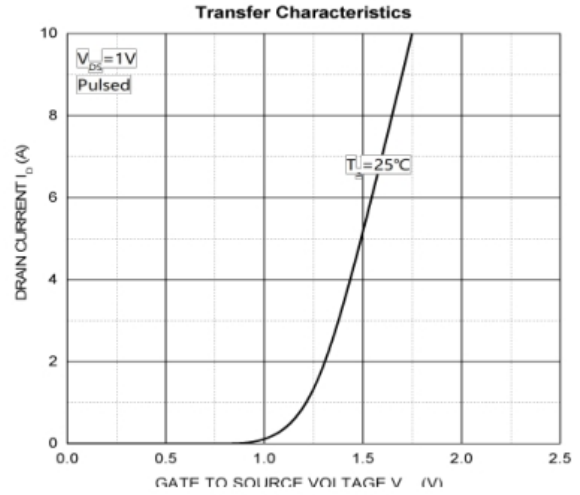
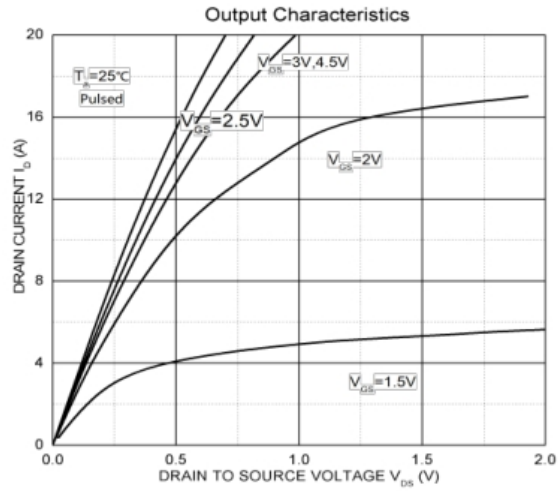
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--|---------------------|---|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | BV (BR)DSS | V _{GS} = 0V, I _D =250μA | 20 | | | V |
| Zero gate voltage drain current | I _{DSS} | V _{DS} =20V, V _{GS} = 0V | | | 1 | uA |
| Gate-body leakage current | I _{GSS} | V _{GS} =±10V, V _{DS} = 0V | | | ±0.1 | uA |
| Gate threshold voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 0.4 | 0.65 | 1 | V |
| Drain-source on-resistance | R _{DS(on)} | V _{GS} =4.5V, I _D =1A | | 60 | 90 | mΩ |
| | | V _{GS} =2.5V, I _D =0.5A | | 70 | 110 | |
| Dynamic Characteristics ⁴⁾ | | | | | | |
| Input capacitance | C _{iss} | V _{DS} =10V, V _{GS} =0V, f=1MHz | | 220 | | pF |
| Output capacitance | C _{oss} | | | 40 | | |
| Reverse transfer capacitance | C _{rss} | | | 20 | | |
| Total gate charge | Q _g | V _{DS} =10V, V _{GS} =4.5V, I _D =2A | | 2.7 | | nC |
| Gate-source charge | Q _{gs} | | | 0.4 | | |
| Gate-drain charge | Q _{gd} | | | 0.5 | | |
| Switching Characteristics ⁴⁾ | | | | | | |
| Turn-on Delay Time | T _{d(on)} | V _{DD} =10V, R _L =3.3Ω, V _{GEN} =4.5V, R _{GEN} =6Ω | | 2.3 | | nS |
| Turn-on Rise Time | T _r | | | 3.1 | | |
| Turn-Off Delay Time | T _{d(off)} | | | 20 | | |
| Turn-Off Fall Time | t _f | | | 2.5 | | |
| Source-Drain Diode Characteristics ⁴⁾ | | | | | | |
| Diode Forward voltage | V _{SD} | I _S =1A, V _{GS} =0V | | | 1.2 | V |

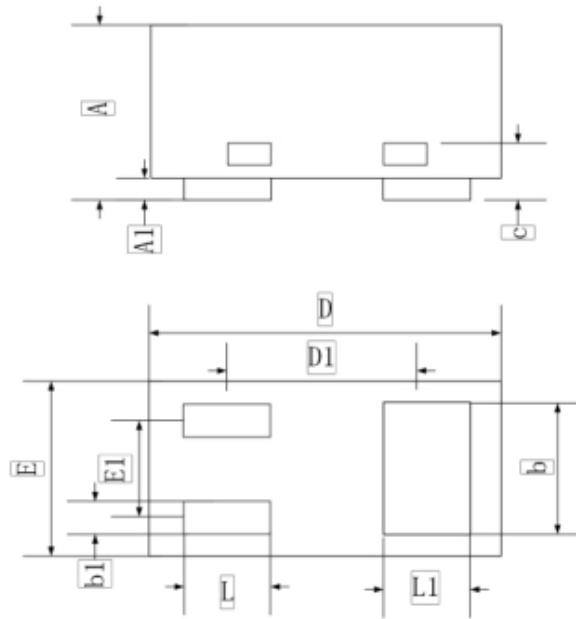
Notes:

1. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. These parameters have no way to verify.

Typical Characteristics



DFN1006-3L Package Information



| Symbol | Dimensions in millimeters | |
|--------|---------------------------|------|
| | Min. | Max. |
| A | 0.46 | 0.51 |
| A1 | 0 | 0.05 |
| b | 0.45 | 0.55 |
| b1 | 0.1 | 0.2 |
| c | 0.08 | 0.18 |
| D | 0.95 | 1.05 |
| D1 | 0.65 | |
| E | 0.55 | 0.65 |
| E1 | 0.325 | |
| L | 0.2 | 0.3 |
| L1 | 0.2 | 0.3 |